AMP5033
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB linear GaAsFET hybrid design
Design for narrow Ka Band applications
Suitable for all single channel modulations standards
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	29.75 GHz ±250 MHz	
Power Output	10 Watt Min	4W Min @ 24-25GHz
Power Gain	40 dB Min	
Power Gain Flatness	1 dB p-p Max	Constant input power
Input / Output Return Loss	10 dB Min	Relative to 50 Ohm
Harmonics	>20 dBc Typ	At rated Pout
Non Harmonics Spurious	>60 dBc Min	
Operating Voltage	28 VDC Nom	
Current Consumption	3.8 Amp Typ	At rated Pout
Max Input Power	+3 dBm	Without damage
Load VSWR Protection	5 : 1	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non Condensation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	110 X 110 X 27 mm	Excluding Connectors
Weight	0.7 Kg	
RF Connectors In/Out	2.9 mm female	
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	Reserved
2	N/C	Reserved
3	CURRENT SENSOR	I_D @ 20mV/100mA Typ
4	TEMP SENSOR	V_T @ 10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
6,7	VDD	28VDC
8,9	GND	Ground

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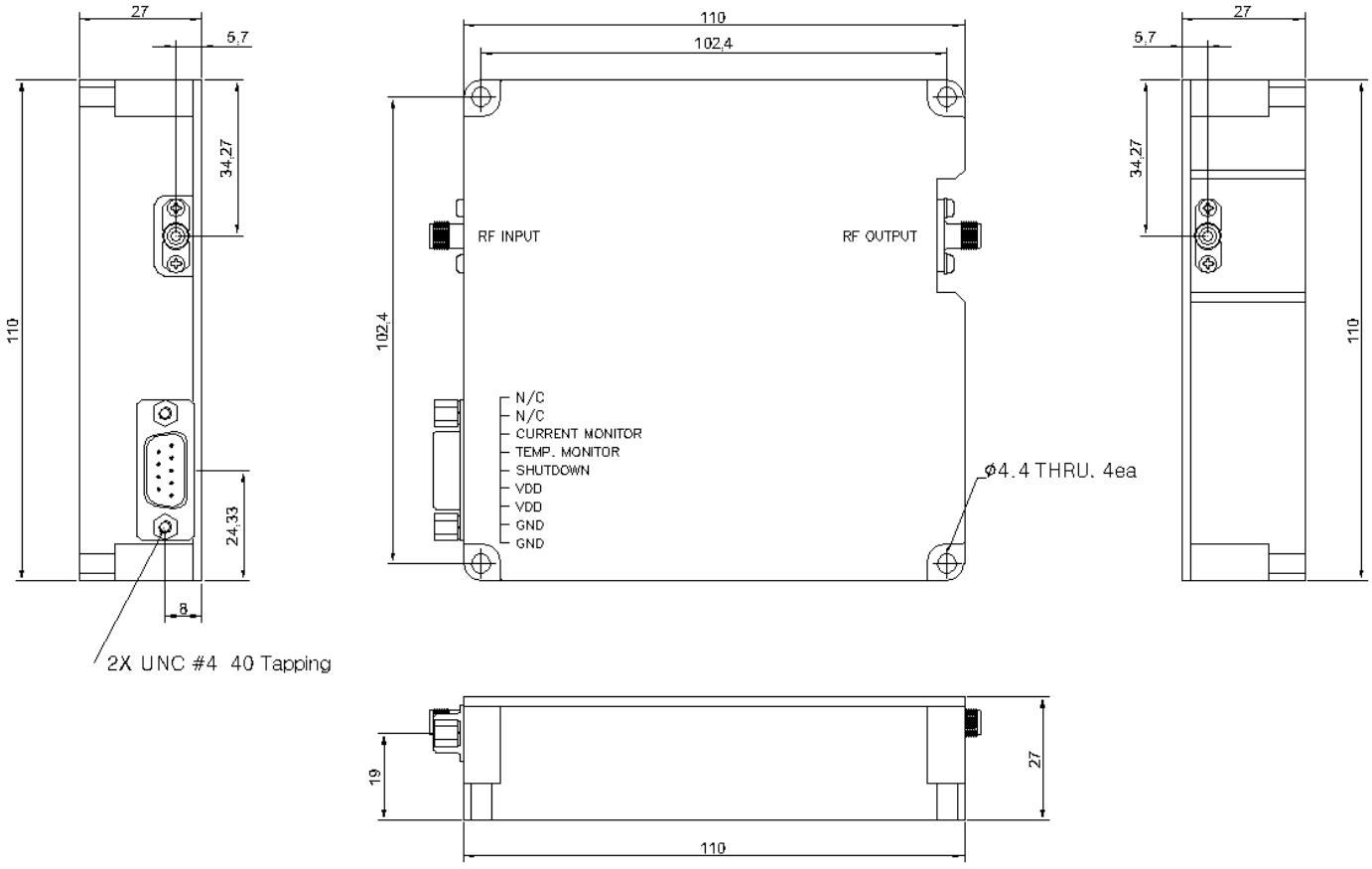
OUTLINE DRAWING